

N-Channel 30-V (D-S) MOSFET

Key Features:

- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

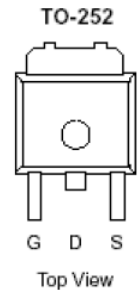
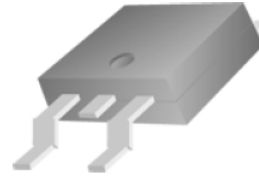
Typical Applications:

- DC/DC Conversion
- Power Routing
- Motor Drives

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (m Ω)	I_D (A)
30	9 @ $V_{GS} = 10V$	61
	16 @ $V_{GS} = 4.5V$	46



RoHS
COMPLIANT
HALOGEN
FREE



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^a	I_D	61	A
Pulsed Drain Current ^b	I_{DM}	200	
Continuous Source Current (Diode Conduction) ^a	I_S	50	A
Power Dissipation ^a	P_D	50	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	3	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

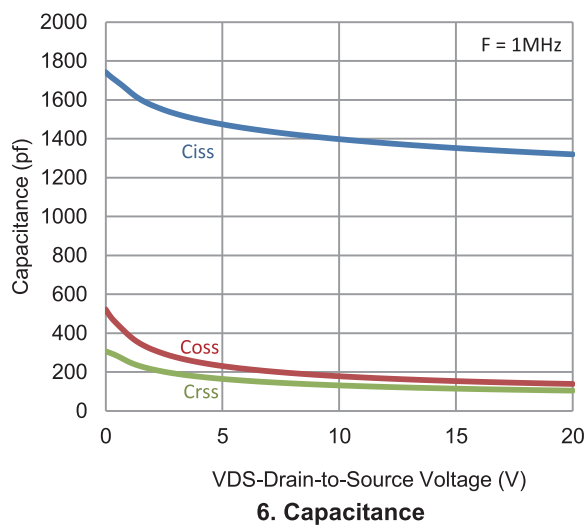
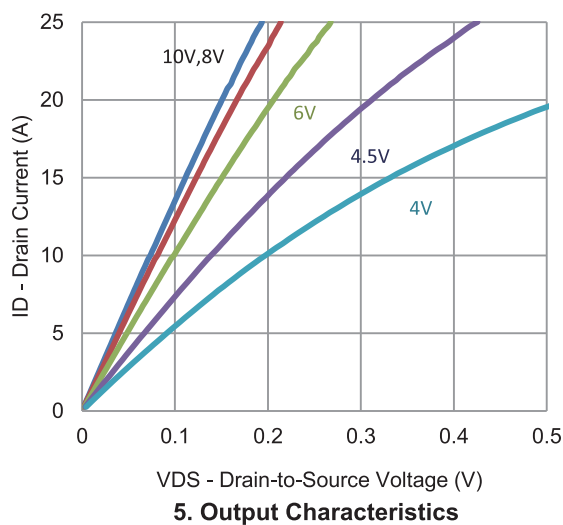
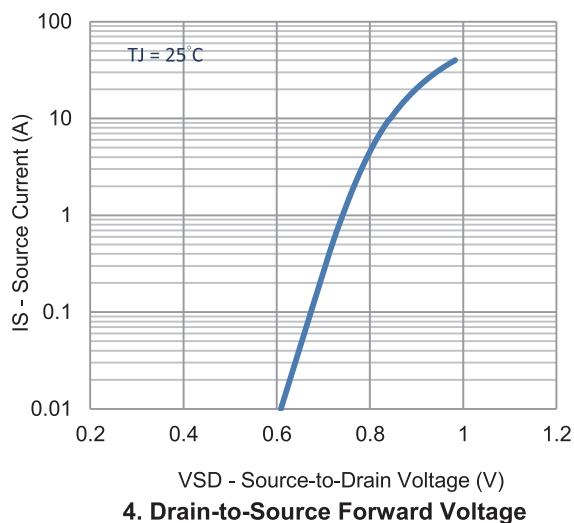
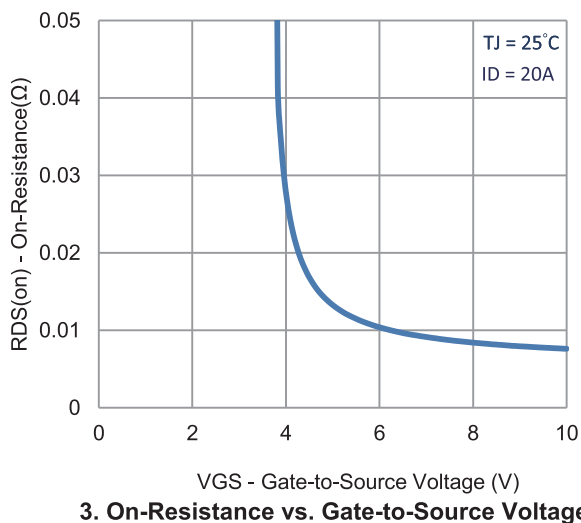
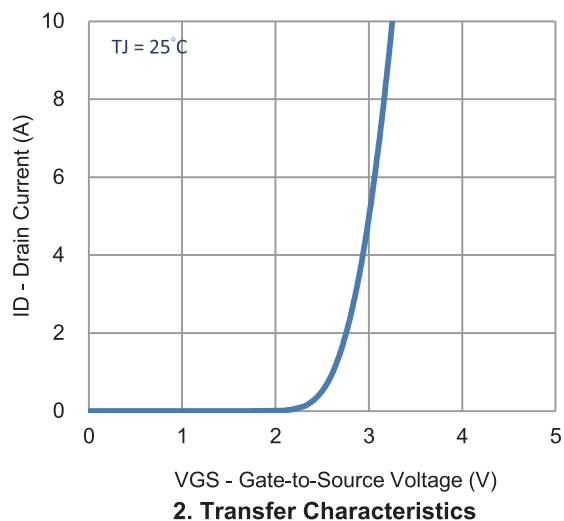
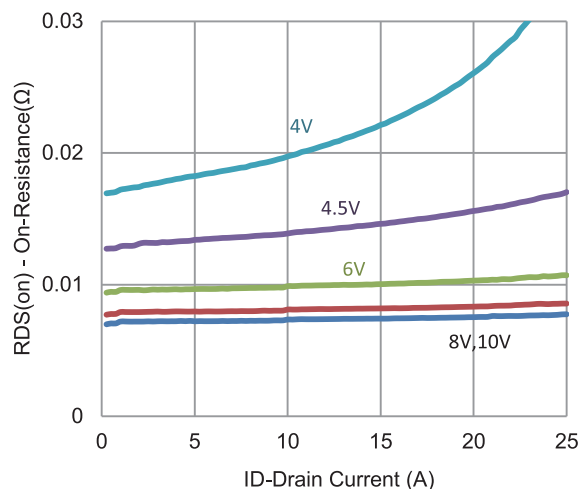
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24 V, V_{GS} = 0 V$			1	μA
		$V_{DS} = 24 V, V_{GS} = 0 V, T_J = 55^\circ C$			25	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 V, V_{GS} = 10 V$	90			A
Drain-Source On-Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10 V, I_D = 20 A$			9	m Ω
		$V_{GS} = 4.5 V, I_D = 16 A$			16	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 V, I_D = 20 A$		13		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 25 A, V_{GS} = 0 V$		0.92		V
Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = 15 V, V_{GS} = 4.5 V,$ $I_D = 20 A$		9.5		nC
Gate-Source Charge	Q_{gs}			4.9		
Gate-Drain Charge	Q_{gd}			4.4		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 15 V, R_L = 0.8 \Omega,$ $I_D = 20 A,$ $V_{GEN} = 10 V, R_{GEN} = 6 \Omega$		6		ns
Rise Time	t_r			6		
Turn-Off Delay Time	$t_{d(off)}$			27		
Fall Time	t_f			8		
Input Capacitance	C_{iss}	$V_{DS} = 15 V, V_{GS} = 0 V, f = 1 Mhz$		1352		pF
Output Capacitance	C_{oss}			153		
Reverse Transfer Capacitance	C_{rss}			114		

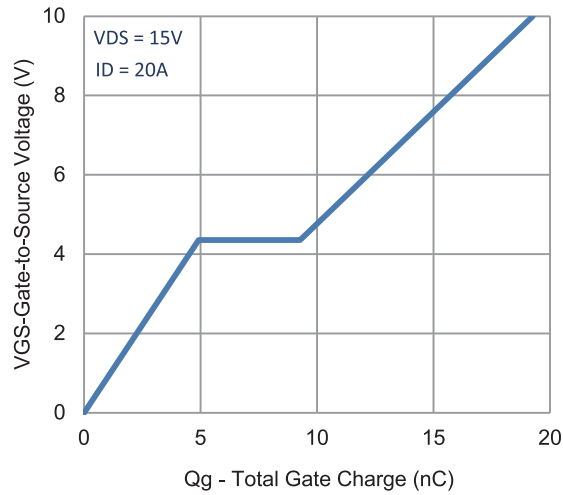
Notes

- a. Pulse test: PW ≤ 300us duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

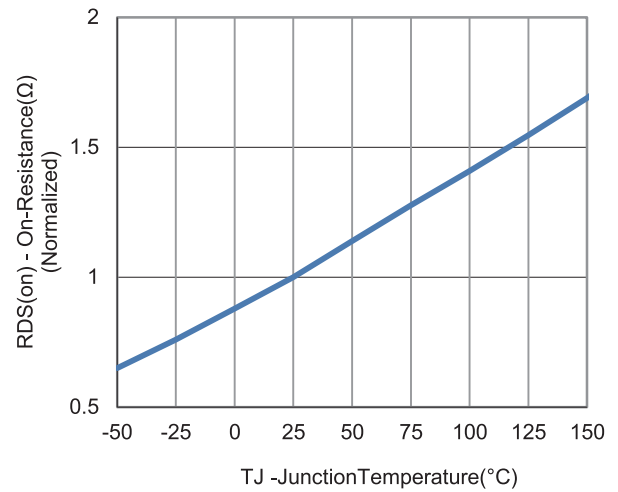
Typical Electrical Characteristics



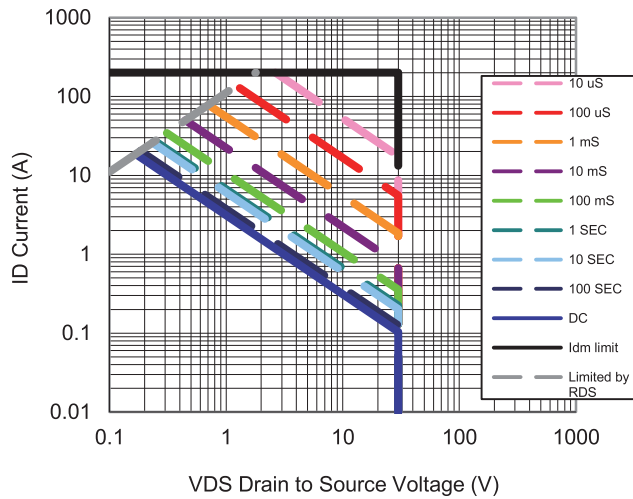
Typical Electrical Characteristics



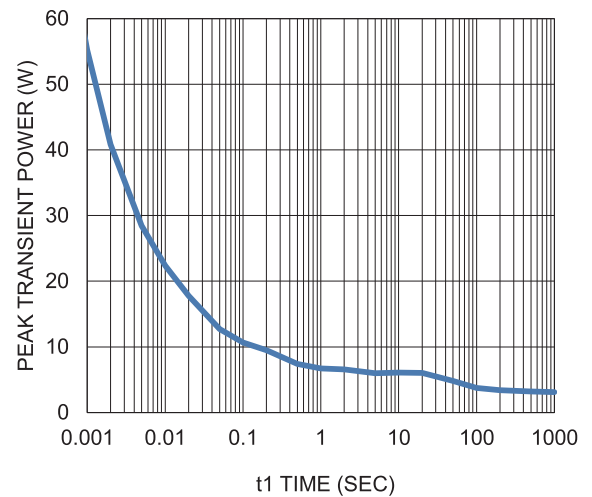
7. Gate Charge



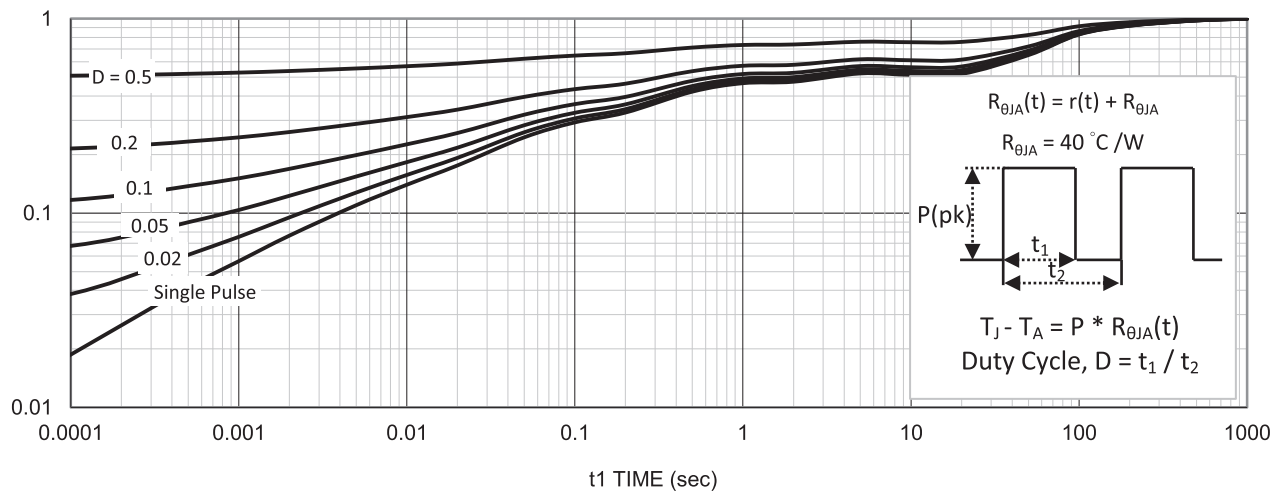
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

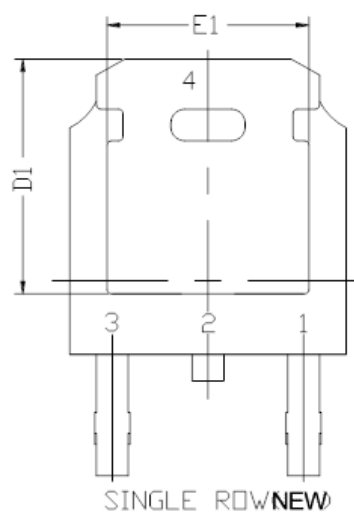
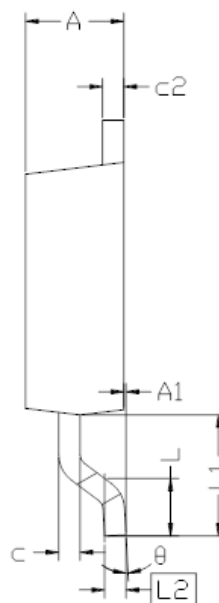
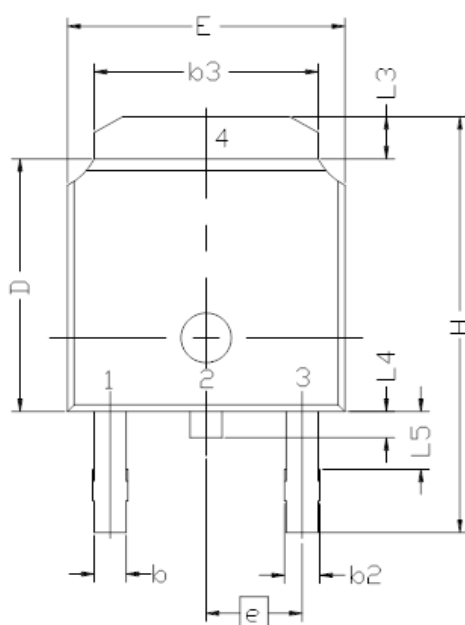


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2.743 REF		
L2	0.508 BSC		
L3	0.89	--	1.27
L4	0.64	--	1.01
L5	--	--	--
D	6.00	6.10	6.223
H	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2.286 BSC		
A	2.20	2.30	2.38
A1	0	--	0.127
c	0.45	0.50	0.60
c2	0.45	0.50	0.58
D1	5.30	--	--
E1	4.40	--	--
θ	0°	--	10°

Note:

1. All Dimension Are In mm.
2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.